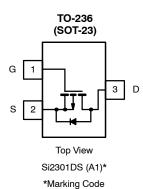


# P-Channel 1.25-W, 2.5-V MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)}$ ( $\Omega$ )	I <sub>D</sub> (A)	
-20	0.130 @ V <sub>GS</sub> = -4.5 V	-2.3	
	0.190 @ V <sub>GS</sub> = -2.5 V	-1.9	



Ordering Information: Si2301DS-T1

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	-20	v		
Gate-Source Voltage		V <sub>GS</sub>	±8	v		
0 11 D 1 0 1 T 1 1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	T <sub>A</sub> = 25°C		-2.3			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>b</sup>	T <sub>A</sub> = 70°C	l <sub>D</sub>	-1.5			
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	-10	A		
Continuous Source Current (Diode Conduction) <sup>b</sup>		I <sub>S</sub>	-1.6			
D	T <sub>A</sub> = 25°C		1.25			
Power Dissipation <sup>b</sup>	T <sub>A</sub> = 70°C	P <sub>D</sub>	0.8	w		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient <sup>b</sup>		100		
Maximum Junction-to-Ambient <sup>c</sup>	$R_{thJA}$	166	°C/W	

#### Notes

- Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board,  $t \le 5$  sec. Surface Mounted on FR4 Board.

 $For \ \ SPICE \ model \ information \ via \ the \ \ Worldwide \ \ Web: \ \ http://www.vishay.com/www/product/spice.htm$ 

Document Number: 70627 S-31990—Rev. E, 13-Oct-03 www.vishay.com

## Si2301DS

## Vishay Siliconix



Parameter	T	S OTHERWISE NOTED)	Limita			T
				Limits		
	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.45			] V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±8 V			± 100	nA
		$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	
O- 04-4- Di- 049		$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-6			Α
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	-3			
	_	$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.105	0.130	Ω
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -2.5$ V, $I_D = -2.0$ A		0.145	0.190	
Forward Transconductance <sup>a</sup>	9fs	$V_{DS} = -5 \text{ V}, I_{D} = -2.8 \text{ A}$		6.5		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-0.80	-1.2	٧
Dynamic <sup>b</sup>						
Total Gate Charge	Qg			5.8	10	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_D \cong -2.8 \text{ A}$		0.85		nC
Gate-Drain Charge	$Q_{gd}$			1.70		
Input Capacitance	C <sub>iss</sub>			415		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -6 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		223		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			87		
Switching <sup>c</sup>			•			•
Turn-On Time	t <sub>d(on)</sub>			13.0	25	
	t <sub>r</sub>	$V_{DD} = -6 \text{ V, } R_L = 6 \Omega$		36.0	60	ne
Turn-Off Time	t <sub>d(off)</sub>			42	70	ns
rum-Oii rime	t <sub>f</sub>			34	60	

#### Notes

- notes

  a. Pulse test: PW ≤300 µs duty cycle ≤2%.

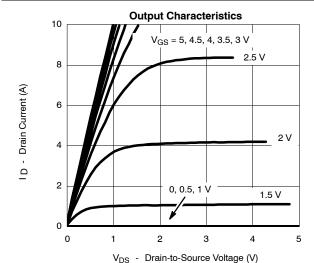
  b. For DESIGN AID ONLY, not subject to production testing.

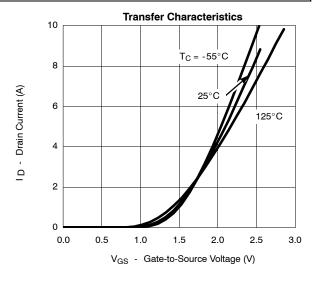
  c. Switching time is essentially independent of operating temperature.

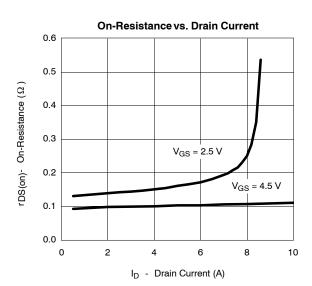


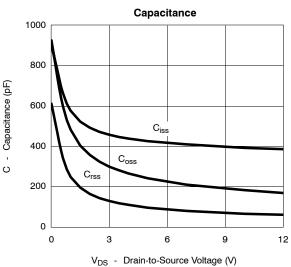
## **Vishay Siliconix**

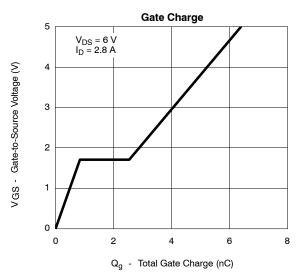
### TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

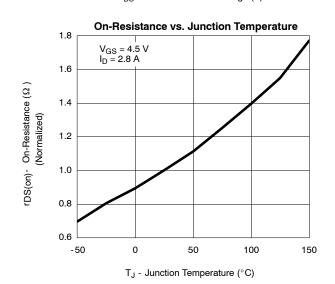








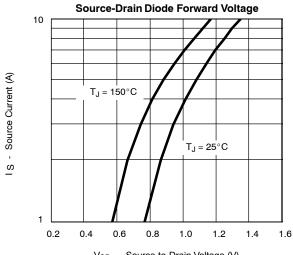




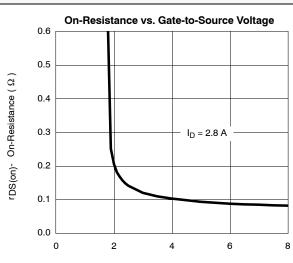
## **Vishay Siliconix**



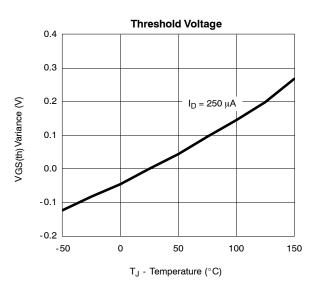
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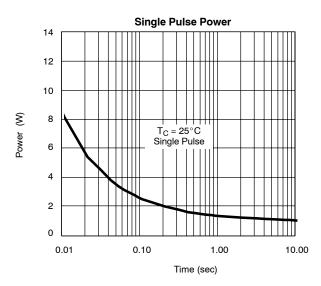


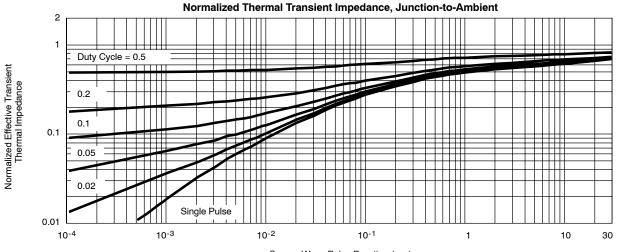
V<sub>SD</sub> - Source-to-Drain Voltage (V)



V<sub>GS</sub> - Gate-to-Source Voltage (V)







Square Wave Pulse Duration (sec)



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